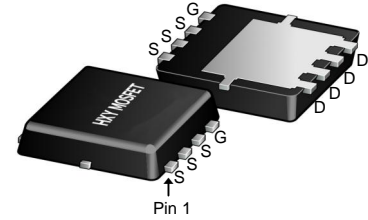




Description

The SI7145DP-T1-GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

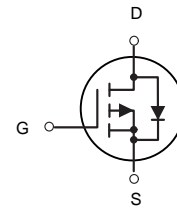


DFN5X6-8L

General Features

$V_{DS} = -30V$ $I_D = -100A$

$R_{DS(ON)} < 4\ m\Omega$ $V_{GS} = -10V$



P-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI7145DP-T1-GE3	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	-100	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	-70	A
I_{DM}	Pulsed Drain Current ²	-250	A
EAS	Single Pulse Avalanche Energy ³	80	mJ
I_{AS}	Avalanche Current	-70	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	120	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	50	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	1.6	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-20A	---	3	4.0	mΩ
		V _{GS} =-4.5V, I _D =-15A	---	4.2	6.0	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	---	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.2	---	Ω
Q _g	Total Gate Charge (-10V)	V _{DS} =-15V, V _{GS} =-10V, I _D =-18A	---	60	---	nC
Q _{gs}	Gate-Source Charge		---	9	---	
Q _{gd}	Gate-Drain Charge		---	15	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, V _{GS} =-10V, R _G =3.3Ω, I _D =-20A	---	17	---	ns
T _r	Rise Time		---	40	---	
T _{d(off)}	Turn-Off Delay Time		---	55	---	
T _f	Fall Time		---	13	---	
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz	---	3450	---	pF
C _{oss}	Output Capacitance		---	255	---	
C _{rss}	Reverse Transfer Capacitance		---	140	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-100	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-20A, di/dt=100A/μs,	---	22	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	72	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=-50V,V_{GS}=-10V,L=0.1mH,I_{AS}=-40A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications , should be limited by total power dissipation
- 6.The maximum current rating is package limited.



Typical Characteristics

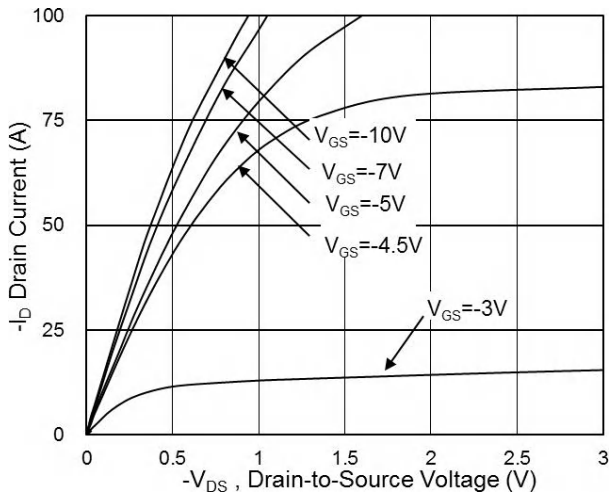


Fig.1 Typical Output Characteristics

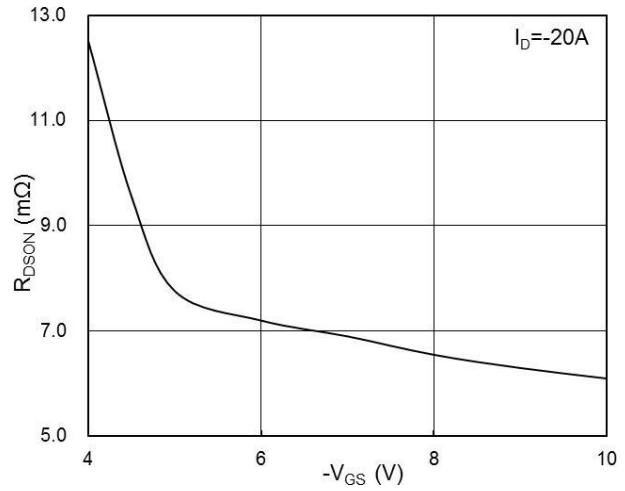


Fig.2 On-Resistance vs G-S Voltage

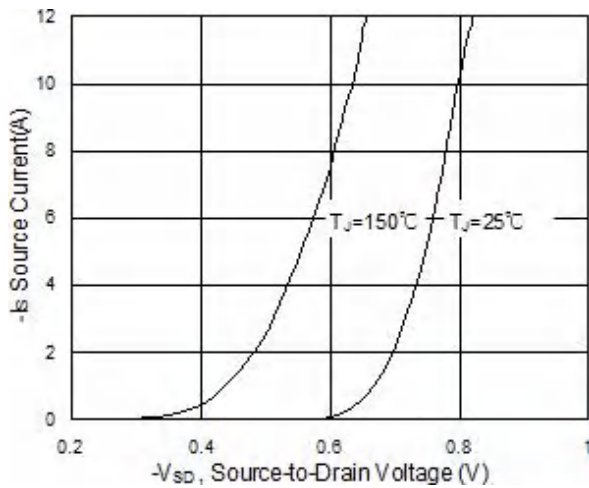


Fig.3 Source Drain Forward Characteristics

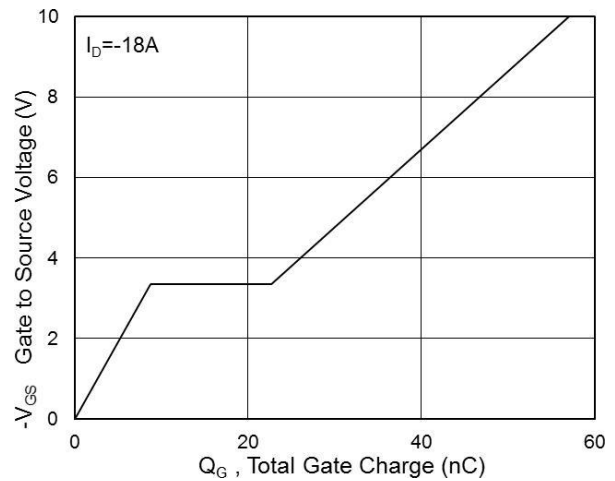


Fig.4 Gate-Charge Characteristics

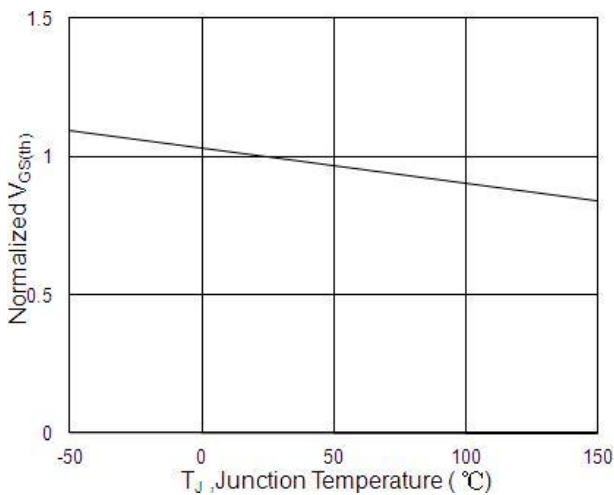


Fig.5 Normalized $-V_{GS(th)}$ vs T_J

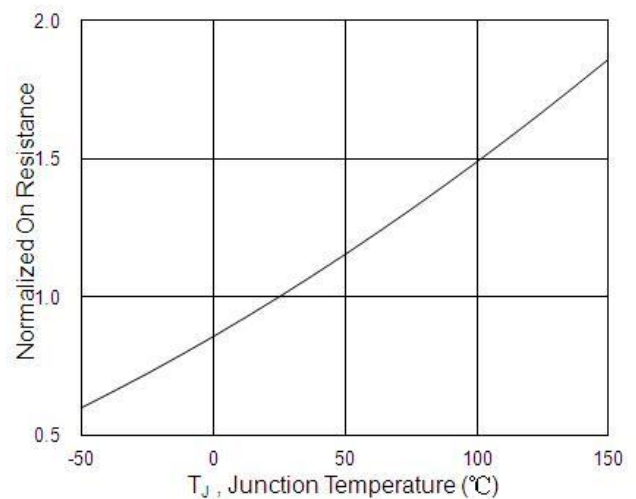


Fig.6 Normalized $R_{DS(on)}$ vs T_J

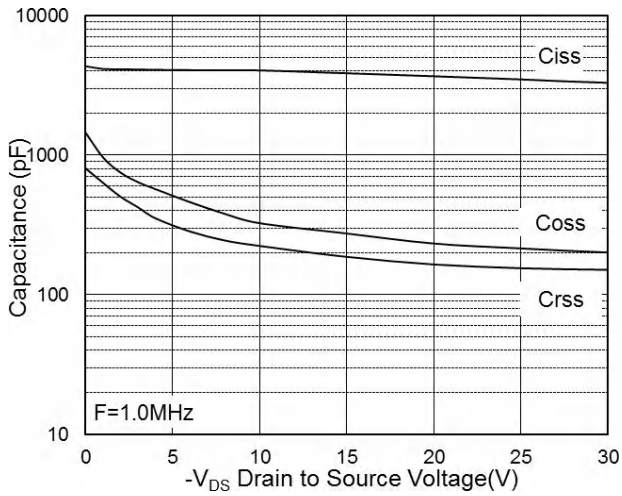


Fig.7 Capacitance

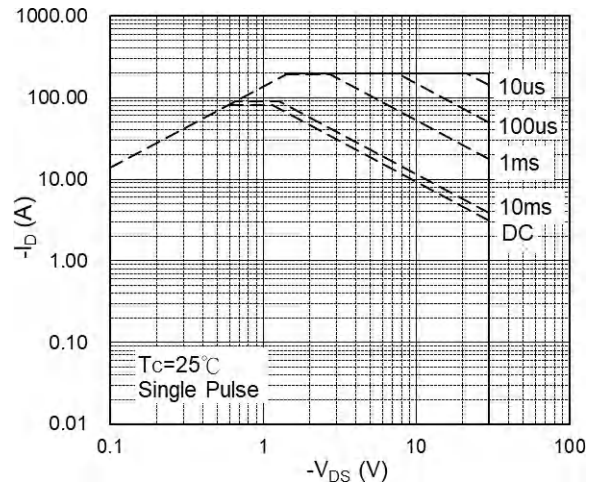


Fig.8 Safe Operating Area

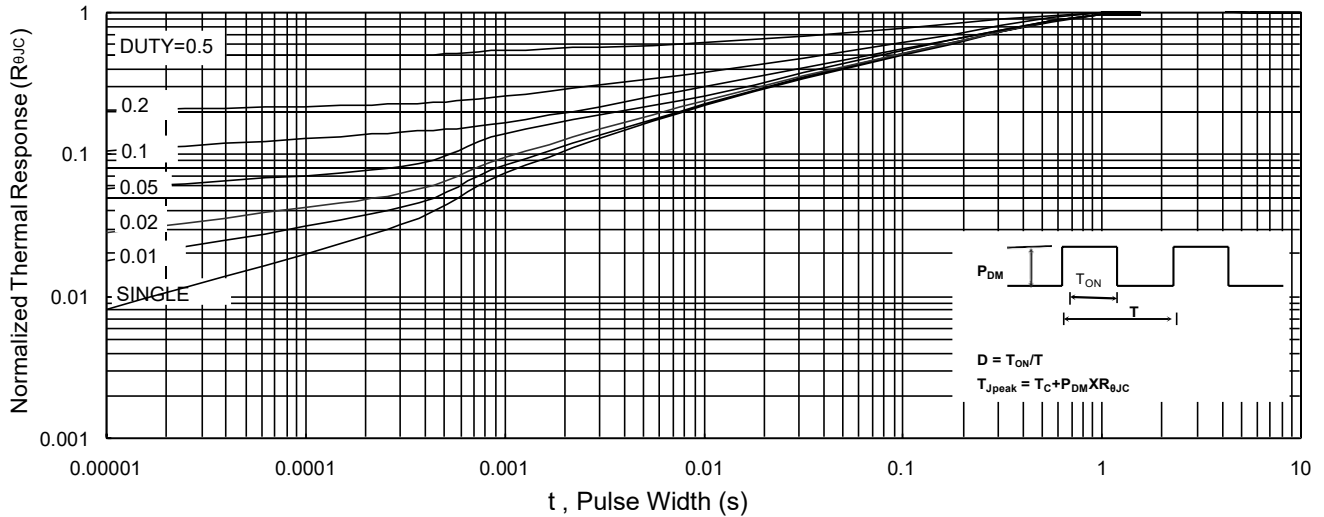


Fig.9 Normalized Maximum Transient Thermal Impedance

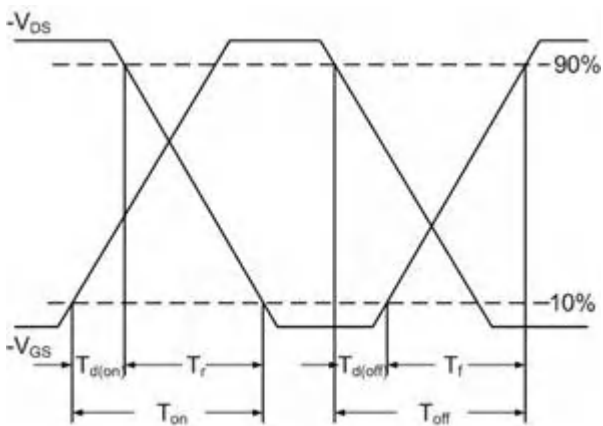


Fig.10 Switching Time Waveform

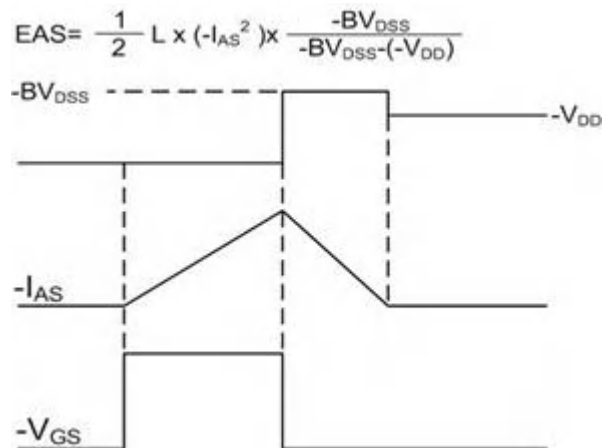
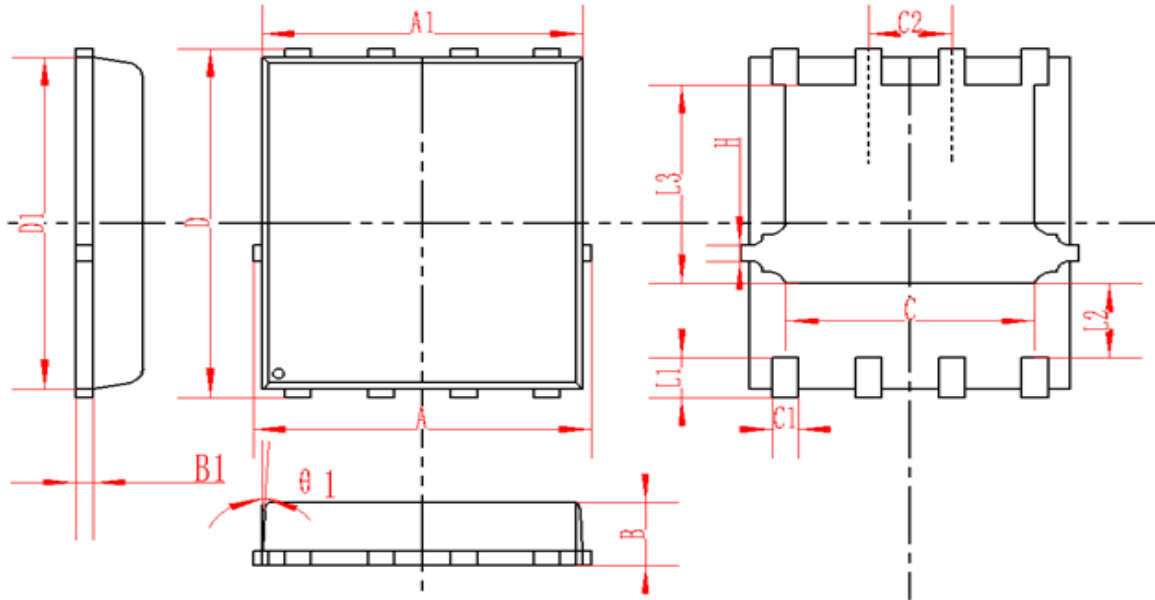


Fig.11 Unclamped Inductive Switching Waveform



DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
$\theta 1$	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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